PNP Epitaxial Planar Silicon Transistor



2SA1865

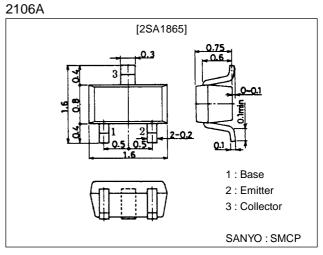
Muting Circuits, Driver Applications

Features

- · On-chip bias resistors (R1=10k Ω , R2=10k Ω).
- Very small-sized package making 2SA1865-applied sets to small and slim.
- · Small ON resistance.
- \cdot High gain-bandwidth product $f_{\text{T}}.$

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|------------------|------------|-------------|------|
| Collector-to-Base Voltage | V _{CBO} | | -15 | V |
| Collector-to-Emitter Voltage | V _{CEO} | | -15 | V |
| Emitter-to-Base Voltage | V _{EBO} | | -10 | V |
| Input Voltage | VIN | | -14 | V |
| Collector Current | IC | | -100 | mA |
| Collector Current (Pulse) | I _{CP} | | -200 | mA |
| Base Current | Ι _Β | | -20 | mA |
| Collector Dissipation | PC | | 150 | mW |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--------------------------|------------------|---|---------|------|------|-------|
| Falanetei | | | min | typ | max | Offic |
| Collector Cutoff Current | ICBO | V _{CB} =-10V, I _E =0 | | | -0.1 | μA |
| Collector Cutoff Current | ICEO | V _{CE} =-10V, I _E =0 | | | -0.5 | μA |
| Emitter Cutoff Current | I _{EBO} | V _{EB} =-5V, I _C =0 | -195 | -250 | -360 | μA |
| DC Current Gain | h _{FE} | V _{CE} =-2V, I _C =-10mA | 50 | | | |
| Gain-Bandwidth Product | fT* | $V_{CE}=-5V, I_{C}=-10mA$ | | 600 | | MHz |
| Output Capacitance | C _{ob*} | V _{CB} =-10V, f=1MHz | | 0.9 | | pF |

* : Charactersistic of the constituent transistor.

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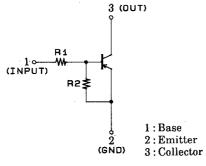
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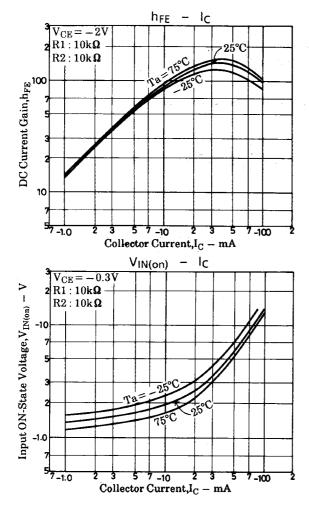
SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

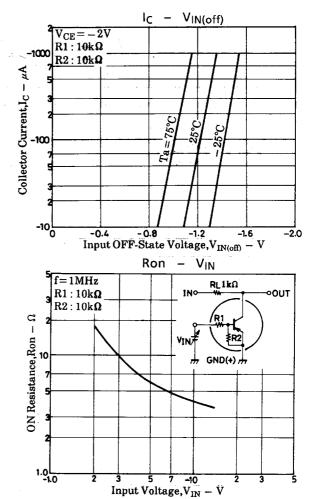
| Parameter | Symbol | Conditions | | Ratings | | |
|---|-----------------------|---|------|---------|------|------|
| | Symbol | | min | typ | max | Unit |
| Collector-to-Emitter Saturation Voltage | V _{CE(sat)} | I _C =-2.5mA, I _B =-0.25mA | | -20 | -60 | mV |
| Collector-to-Base Breakdown Voltage | V _(BR) CBO | I _C =-10µA, I _E =0 | -15 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | I _C =−1mA, R _{BE} =∞ | -15 | | | V |
| Input OFF-State Voltage | V _{IN(off)} | V _{CE} =-2V, I _C =-100µA | -0.8 | -1.2 | -1.5 | V |
| Input ON-State Voltage | V _{IN(on)} | V _{CE} =-0.3V, I _C =-10mA | -1.0 | -2.0 | -4.0 | V |
| Input Resistance | R1 | | 7.0 | 10 | 13 | kΩ |
| Resistance Ratio | R1/R2 | | 0.9 | 1.0 | 1.1 | |
| On Resistance | R _{on} | V _{IN} =–5V, f=1MHz | | 6.0 | | Ω |

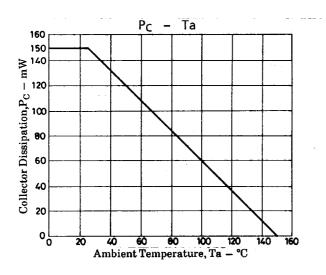
Marking : BA

Electrical Connection









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